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(54) **THREE-DIMENSIONAL MEMORY DEVICE
WORDLINES WITH REDUCED BLOCKING
LAYER DAMAGE**

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(57) **ABSTRACT**

A method includes obtaining a base structure of a three-dimensional (3D) memory device, forming, on the base structure, a blocking layer including a high-k dielectric material, and forming, on the blocking layer, a wordline for the 3D memory device including molybdenum using an atomic layer deposition (ALD) process.

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